

SYSTEM AND METHOD FOR INTEGRATED OXIDE REMOVAL AND
PROCESSING OF A SEMICONDUCTOR WAFER

5 ABSTRACT OF THE DISCLOSURE

10 An integrated oxide removal and processing system
 (10) includes a process module (30) that may
 intentionally add at least one film layer to a single
 semiconductor wafer (32). The integrated oxide removal
 and processing system (10) also includes a transfer
 chamber module (20) used to align the semiconductor wafer
 (32) for the process module (30). The transfer chamber
 module (20) may expose the semiconductor wafer (32) to a
 vaporous solution that is inert with respect to the
15 semiconductor wafer (32) and operable to remove an oxide
 layer (110) therefrom. More specifically, the
 semiconductor wafer (32) includes silicon. In a further
 embodiment, the vaporous solution includes HF. In yet a
 further embodiment, the vaporous solution includes .049%
20 to 49% HF.